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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use several sheets if necessary)

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APPLICANT  
Atsushi YAMAGUCHI et al.

FILING DATE  
March 26, 2001

GROUP  
2826

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA					
	AB					
	AC					

**FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION**

	DOCUMENT NO.	PUBL. DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANSLATION YES NO
R. N.	AH A 2000-77785	03/00	JP			
A. S.	AI A 2000-58915	02/00	JP			
A. S.	AJ A 2000-21789	01/00	JP			
A. S.	AK A 2000-4063	01/00	JP			
	AL					
	AM					
	AN					

**OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication)**

R. N.	AM	Shuji Nakamura et al., "InGaN/GaN/AlGaIn-Based Laser-Diodes with Modulation-Doped Strained-Layer Superlattices," <u>Jpn. J. Appl. Phys.</u> , V. 36, 1997, pp. 1568-1571.
A. S.	AN	<u>Applied Physics</u> , V. 68, No. 7, 1999, pp. 793-796.
	AO	

EXAMINER

DATE CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered.  
Include copy of this form with next communication to applicant.